



Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

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Document Number (Optional)

IME-03-009

Application Number

10/767,275

Applicant

Ming Fu Li et al.

Filing Date

01/29/04

Drawn At Unit

U. S. PATENT DOCUMENTS

PATENT	DOCUMENT NUMBER	DATE	TITLE	CLASS	SUBCLASS	ANNO DATE IF APPROPRIATE
ON	6208555	3/27/01	Noble	365	159	3/30/99
	6512274	1/28/03	King et al.	257	369	6/22/00
	6528370	3/4/03	Suzuki et al.	438	257	7/29/02
	5466949	11/14/95	Okuno	257	25	8/4/94
	5616515	4/1/97	Okuno	438	478	6/7/95
	6239450	5/29/01	Harvey et al.	257	49	1/14/99
	5606177	2/25/97	Wallace et al.	257	25	12/6/94
ON	6208555	3/27/01	Noble	365	159	3/30/99

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
ON	EP 1 684 56 A2	1/2/02	European Patent App.	H01L	29/788		
ON	0 668 618 A2	5/19/94	European Patent App.	H01L	29/88		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

ON	L.L. Chang et al., "Resonant tunneling in the semiconductor double barriers," Appl. Phys. Lett., Vol. 24, pp. 593-595, June 1974.
ON	J.P. Sun et al., "Resonant Tunneling Diodes: Models and Properties," Proc. of the IEEE, Vol. 86, No. 4, April 1998, pp. 641-661, (SIA).
ON	Ikeda et al., "Resonant tunneling characteristics in SiO ₂ /Si double barrier structures in a wide range of applied voltage," Appl. Phys. Lett., Vol. 83, No. 7, Aug. 2003, pp. 1456-1458.

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DATE CONSIDERED

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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Agreement Number

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Group 1st Unit

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ON	-	Kim et al., "Effect of Barrier Thickness on the Interface and Optical Properties of InGaN/GaN Multiple Quantum Wells", Jpn. J. Appl. Phys, Part 1, 40, 3085 (2001).
ON	-	Huang et al., "Sub 50-nm FinFET: PMOS", IEDM 99-67, 3.4.1 to 3.4.4.
ON	-	U.S. Patent App. Pub. US 2003/0049894 A1 to Berger et al. Pub. 3/13/03,

Filed 8/24/01, US Cl. 438/183.

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Group 2: Unit

INFORMATION DISCLOSURE CITATION
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U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS (Including Author, Title, Date, Portion or Pages, Etc.)

ON	-	Wang et al., "Self-Aligned (Top and Bottom) Double-Gate MOSFET with a 25 nm Thick Silicon Channel," 1997 IEDM Technical Digest, pp. 16.6.1 to 16.6.4.
ON	-	Wilk et al., "High-k gate dielectrics: Current status and materials properties considerations," J. Appl. Phys., Vol. 89, No. 10, May 15, 2001, pp. 5243-5275.

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